

2N7002BKV

60 V, 340 mA dual N-channel Trench MOSFET

Rev. 2 — 22 September 2010

Product data sheet

1. Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V	[1] -	-	340	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 500 \text{mA}$	-	1	1.6	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

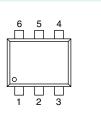


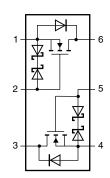
2N7002BKV **Nexperia**

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Pinning information

Table 2. **Pinning** Simplified outline Pin **Symbol** Description 1 S1 source 1 2 G1 gate 1 3 D2 drain 2 4 S2 source 2 G2 5 gate 2 D1 drain 1





Graphic symbol

017aaa055

Ordering information 3.

Table 3. **Ordering information**

Type number	Package				
	Name	Description	Version		
2N7002BKV	-	plastic surface-mounted package; 6 leads	SOT666		

Marking 4.

Table 4. Marking codes

3	
Type number	Marking code
2N7002BKV	ZG

Limiting values 5.

Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • • • • • • • • • • • • • • • • • • •	,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	sistor				
V_{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D	drain current	V _{GS} = 10 V	<u>[1]</u>		
		T _{amb} = 25 °C	-	340	mA
		T _{amb} = 100 °C	-	240	mA
I_{DM}	peak drain current	$T_{amb} = 25$ °C; single pulse; $t_p \le 10$ μs	-	1.2	Α

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 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	350	mW
			<u>[1]</u> _	410	mW
		T _{sp} = 25 °C	-	1140	mW
Source-dr	ain diode				
Is	source current	T _{amb} = 25 °C	<u>[1]</u> _	340	mA
ESD maxi	imum rating				
V _{ESD}	electrostatic discharge voltage	human body model	<u>[3]</u> _	2000	V
Per devic	e				
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	525	mW
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

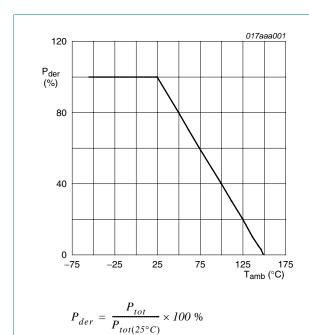
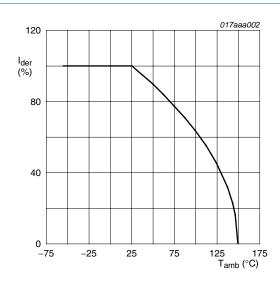


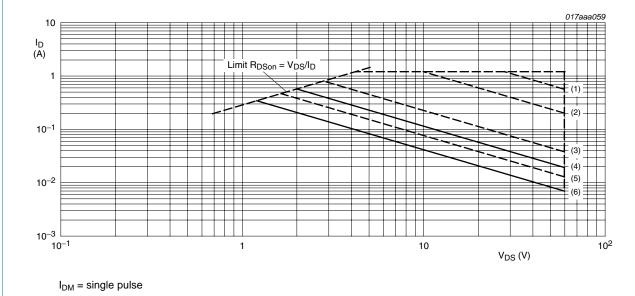
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100~\%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

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- (1) $t_p = 100 \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25 \,^{\circ}\text{C}$
- (5) $t_p = 100 \text{ ms}$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

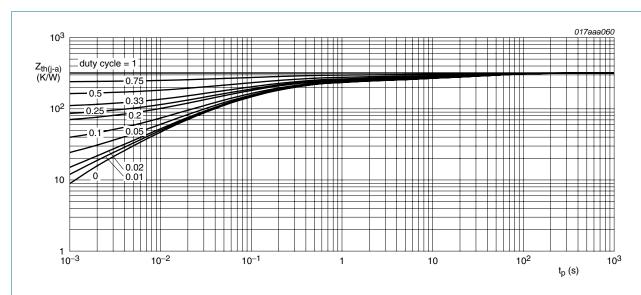
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	315	360	K/W
			[2] _	265	305	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	110	K/W
Per device)					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	240	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

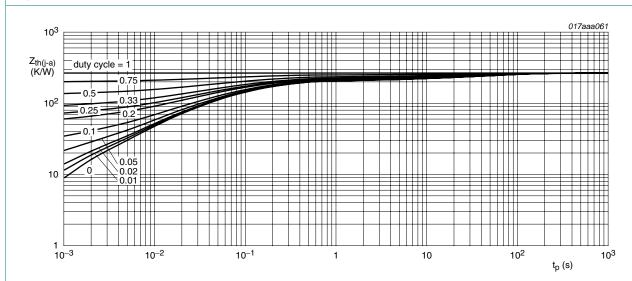
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

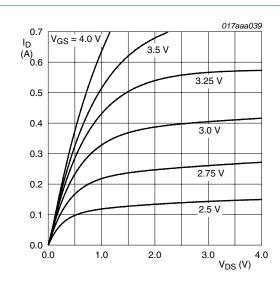
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	10	μΑ
R_{DSon}	drain-source on-state resistance		<u>[1]</u>			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1.3	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}$	-	1	1.6	Ω
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	550	-	mS
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$	-	0.5	0.6	nC
Q_{GS}	gate-source charge	V _{DS} = 30 V; - V _{GS} = 4.5 V	-	0.2	-	nC
Q_{GD}	gate-drain charge	VGS = 4.5 V	-	0.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	33	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	V _{DD} = 50 V;	-	5	10	ns
t _r	rise time	$R_L = 250 \Omega;$ - $V_{GS} = 10 V;$	-	6	-	ns
t _{d(off)}	turn-off delay time	$R_{G} = 6 \Omega$	-	12	24	ns
t _f	fall time		-	7	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

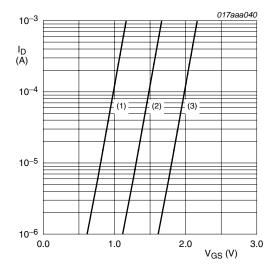
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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 $T_{amb} = 25 \, ^{\circ}C$

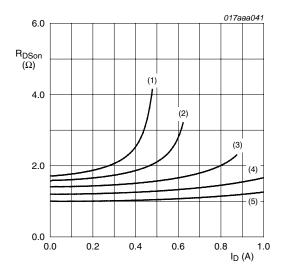
Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

- (1) minimum values
- (2) typical values
- (3) maximum values

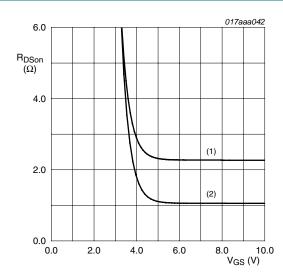
Fig 7. Sub-threshold drain current as a function of gate-source voltage



T_{amb} = 25 °C

- (1) $V_{GS} = 3.25 \text{ V}$
- (2) $V_{GS} = 3.5 \text{ V}$
- (3) $V_{GS} = 4 V$
- (4) $V_{GS} = 5 V$
- (5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values

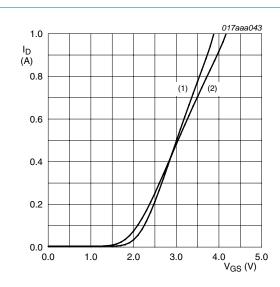


 $I_D = 500 \text{ mA}$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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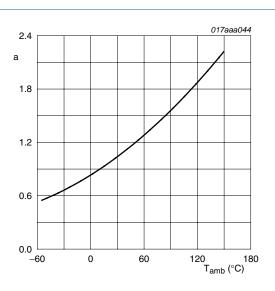


$$V_{DS} > I_{D} \times R_{DSon}$$

(1)
$$T_{amb} = 25 \, ^{\circ}C$$

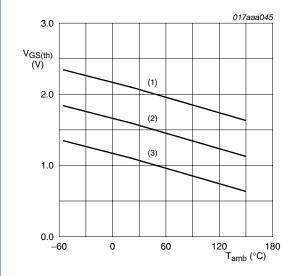
(2)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

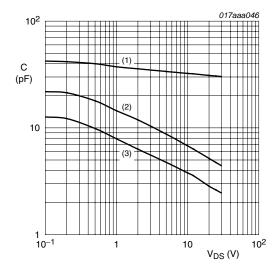
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

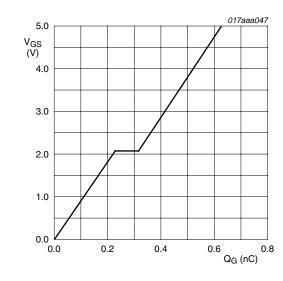
Fig 12. Gate-source threshold voltage as a function of ambient temperature



- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = 300 mA; V_{DD} = 6 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

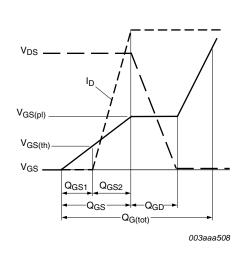
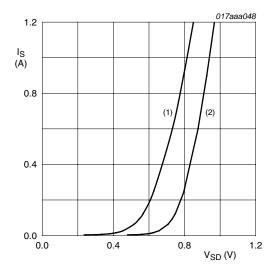


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

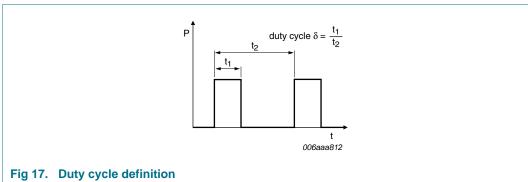
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



2N7002BKV

Package outline

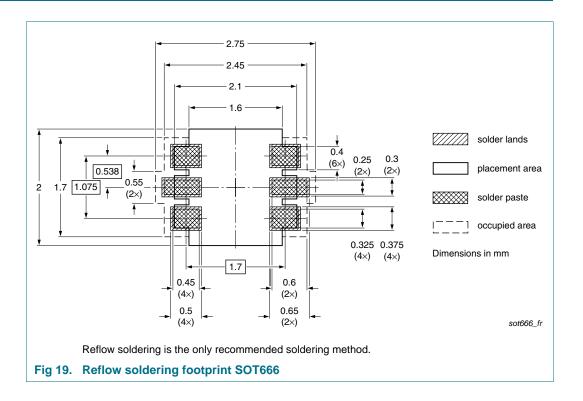
SOT666 Plastic surface-mounted package; 6 leads - A Х pin 1 index С ⊕ w M A detail X 2 mm scale **DIMENSIONS (mm are the original dimensions)** UNIT Ε D Α bp С e₁ H_{E} L_{p} у 0.6 0.27 1.7 1.5 1.7 1.5 0.3 0.1 0.18 1.3 0.5 0.17 0.08 1.1 REFERENCES **EUROPEAN** OUTLINE ISSUE DATE VERSION JEDEC **PROJECTION** IEC JEITA 04-11-08 SOT666

Fig 18. Package outline SOT666

06-03-16

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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
2N7002BKV v.2	20100922	Product data sheet	-	2N7002BKV v.1		
Modifications:	<u>Table 2 "Pinning"</u> : graphic symbol amended					
	<u>'</u>		0 17	lue per transistor amended		
	lable 6 "In	ermal characteristics": typo	for R _{th(j-a)} maximum vai	ue per device amended		
2N7002BKV v.1	20100610	Product data sheet	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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For more information, please visit: http://www.nexperia.com

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